the temperature of the edge of the tray 2 can be reduced, so that the temperature of the edge of the tray 2 and the temperature of the center of the tray 2 can tend to be the same, ensuring uniformity of temperature distribution between the edge of the tray 2 and the center of the tray 2. A controlling of the temperature of the substrate is conducive to improving quality of the epitaxial layer.

[0034] In other embodiments, a specific structure of the temperature control channel 3 and a number of the temperature control channel 3 are not limited to those in the above embodiment. For example, the supporting base 11 can includes a plurality of temperature control channels 3, and the plurality of temperature control channels 3 can be in a zigzag shape.

[0035] Specifically, the temperature control channel 3 can successively include a first segment, a second segment, and a third segment, which can be communicated with each other. A first end of the second segment can be connected to the first segment, and a second end of the second segment can be connected to the third segment. The first segment and the third segment can extend along the direction of the axis of the epitaxial growth device 100, and the second segment can be in a ring shape, and the second segment in the ring shape can be close to the edge of the tray 2. The cooling medium can flow into the temperature control channel 3 via an inlet of the first segment, and cool the edge of the edge of the tray 2 when flowing through the second segment. Then the cooling medium can discharge from the third segment. The temperature control channel 3 with three segments can be easy to import and discharge the cooling medium. By designing the second segment in the ring shape disposed corresponding to the edge of the tray 2, a relatively high temperature at the edge of the tray 2 can be reduced accurately, thereby accurately controlling temperature at corresponding positions.

[0036] In an embodiment of the present invention, referring to FIG. 1, FIG. 2, and FIG. 4, the supporting base 11 can include two temperature control channels 3, the two temperature control channels 3 can be disposed corresponding to two sides of the tray 2 respectively, and the two temperature control channels 3 can control temperatures of the two sides of the tray 2. The two temperature control channels 3 can extend along the direction of the axis of the epitaxial growth device 100 to match with a piping outside the epitaxial growth device 100 for importing and discharging the cooling medium.

[0037] Referring to FIG. 1 to FIG. 4, a mounting groove is disposed on the supporting base 11, a locating column 14 is disposed at an axis of the mounting groove 13, and the locating column 14

of supporting bases 11 can share the induction coil, so as to reduce temperature differences among the plurality of supporting bases 11. Temperatures corresponding to the plurality of trays 2 can be equalized, improving quality of the productions and reducing the variation of the same batch of productions. In other embodiments, the direction along which the plurality of supporting bases 11 are arranged is not limited to the above direction, and the plurality of supporting bases 11 can be arranged along the axis of the induction coil.

[0045] In an embodiment of the present invention, referring to FIG. 1 to FIG. 3, the heating body 1 can include a plurality of sub-heating bases 12. The sub-heating bases 12 can receive the electromagnetic induction of the induction coil to generate heat to ensure sufficient heating of the reaction chamber 5, improving a heating capacity of the heating body 1. The sub-heating bases 12 configured to support the tray 2 can be the above supporting base 11, adjacent two sub-heating bases 12 are combined to form the reaction chamber 5.

[0046] Specifically, referring to FIG. 1 and FIG. 2, the heating body 1 can include three sub-heating bases 12, i.e., a first sub-heating base 121, a second sub-heating base 122, a third sub-heating base 123. Adjacent two sub-heating bases 12 are combined to form a reaction chamber 5, and the second sub-heating base 122 and the third sub-heating base 123 are configured to support the tray 2. In other words, both the second sub-heating base 122 and the third sub-heating base 123 are supporting bases 11. In other embodiments, a specific structure of the heating body 1 is not limited to that described above or shown in the figures. For example, the heating body 1 can also be an integrated structure.

[0047] Furthermore, the heating body 1 can have an axisymmetric structure. The heating body 1 as a whole is approximately symmetrically distributed relative to the axis of the induction coil to reduce temperature differences among the plurality of reaction chambers 5. Specifically, referring to FIG. 1 and FIG. 2, the shape of the first sub-heating base 121 and the shape of the third sub-heating base 123 can be the same. For example, both the first sub-heating base 121 and the third sub-heating base 123 can be in a crescent shape, and the second sub-heating base 122 can be in a plate shape. The first sub-heating base 121 and the third sub-heating base 123 are combined to form a neatly cylindrical structure, and a side wall of the cylindrical structure is sufficiently close to a side of the induction coil, resulting in that the induction coil has good magnetic coupling with the heating base 12. In other embodiments, shapes of the first sub-heating base 121 and the third sub-heating base 123 are not limited to the above shape. For